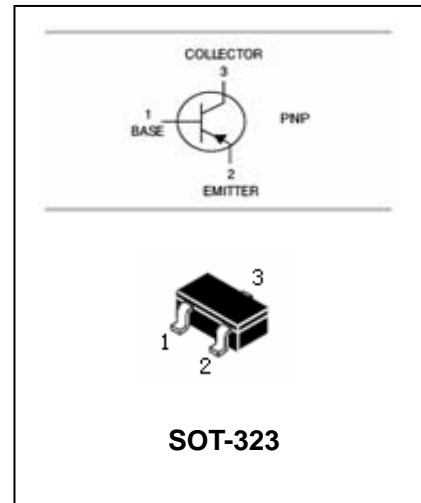


## PNP Silicon Epitaxial Planar Transistor

## 2SA1577W

### FEATURES

- Power dissipation.( $P_C=200\text{mW}$ )
- Excellent  $H_{FE}$  Linearity.



### APPLICATIONS

- General purpose application.

### ORDERING INFORMATION

Type No.	Marking	Package Code
2SA1577W	HP/HQ/HR	SOT-323

### MAXIMUM RATING @ $T_a=25^\circ\text{C}$ unless otherwise specified

Symbol	Parameter	Value	Units
$V_{CBO}$	Collector-Base Voltage	-40	V
$V_{CEO}$	Collector-Emitter Voltage	-32	V
$V_{EBO}$	Emitter-Base Voltage	-5	V
$I_C$	Collector Current -Continuous	-500	mA
$P_C$	Collector Dissipation	200	mW
$T_j, T_{stg}$	Junction and Storage Temperature	-55~150	$^\circ\text{C}$

**PNP Silicon Epitaxial Planar Transistor****2SA1577W****ELECTRICAL CHARACTERISTICS @ Ta=25°C unless otherwise specified**

Parameter	Symbol	Test conditions	MIN	TYP	MAX	UNIT
Collector-base breakdown voltage	$V_{(BR)CBO}$	$I_C=-100\mu A, I_E=0$	-40			V
Collector-emitter breakdown voltage	$V_{(BR)CEO}$	$I_C=-1mA, I_B=0$	-32			V
Emitter-base breakdown voltage	$V_{(BR)EBO}$	$I_E=-100\mu A, I_C=0$	-5			V
Collector cut-off current	$I_{CBO}$	$V_{CB}=-20V, I_E=0$			-1	$\mu A$
Emitter cut-off current	$I_{EBO}$	$V_{EB}=-4V, I_C=0$			-1	$\mu A$
DC current gain	$h_{FE}$	$V_{CE}=-3V, I_C=-10mA$	82		390	
Collector-emitter saturation voltage	$V_{CE(sat)}$	$I_C=-100mA, I_B=-10mA$			-0.4	V
Transition frequency	$f_T$	$V_{CE}=-5V, I_C=-20mA$ $f=100MHz$	200			MHz
Collector output capacitance	$C_{ob}$	$V_{CB}=-10V, I_E=0, f=1MHz$		7		pF

**CLASSIFICATION OF  $h_{FE}$** 

Rank	P	Q	R
Range	82-180	120-270	180-390
marking	HP	HQ	HR

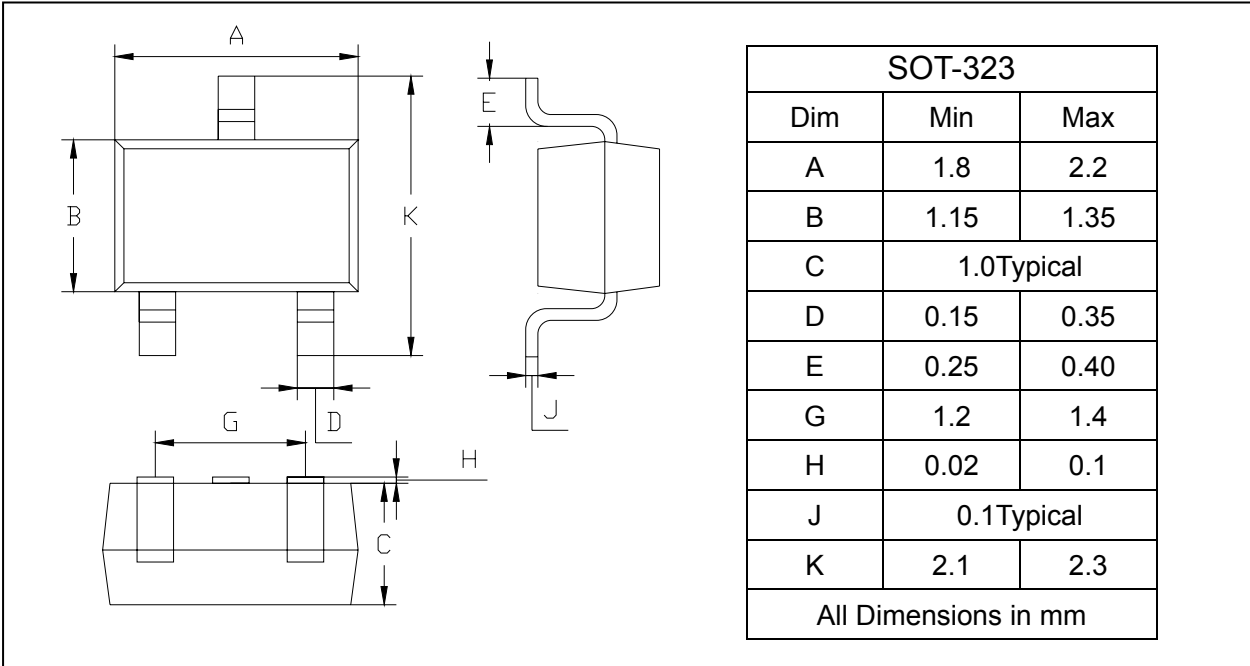
## PNP Silicon Epitaxial Planar Transistor

## 2SA1577W

### PACKAGE OUTLINE

Plastic surface mounted package

SOT-323



### PACKAGE INFORMATION

Device	Package	Shipping
2SA1577W	SOT-323	3000/Tape&Reel